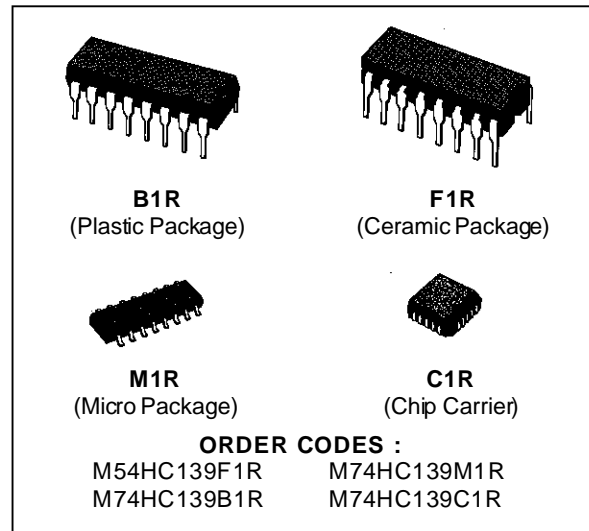


DUAL 2 TO 4 DECODER/DEMULTIPLEXER

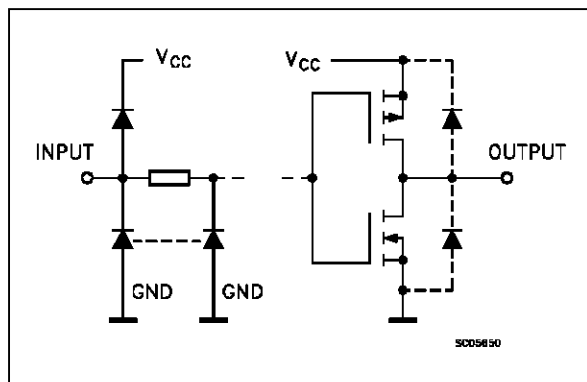
- HIGH SPEED
 $t_{PD} = 12 \text{ ns (TYP.) AT } V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION
 $I_{CC} = 4 \mu\text{A (MAX.) AT } T_A = 25 \text{ }^\circ\text{C}$
- HIGH NOISE IMMUNITY
 $V_{NIH} = V_{NIL} = 28 \% V_{CC} \text{ (MIN.)}$
- OUTPUT DRIVE CAPABILITY
10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
 $|I_{OH}| = |I_{OL}| = 4 \text{ mA (MIN.)}$
- BALANCED PROPAGATION DELAYS
 $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
 $V_{CC} \text{ (OPR)} = 2 \text{ V TO } 6 \text{ V}$
- PIN AND FUNCTION COMPATIBLE
WITH 54/74LS139



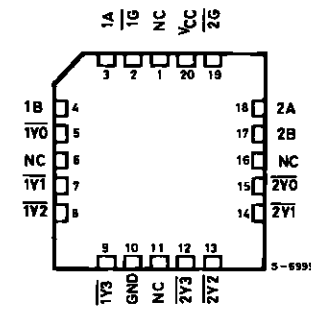
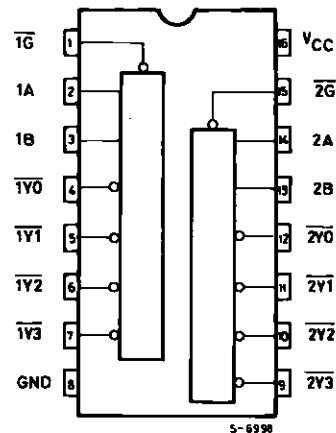
DESCRIPTION

The M54/74HC139 is a high speed CMOS DUAL TWO LINE TO FOUR LINE DECODER/DEMULTIPLEXER fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. The active low enable input can be used for gating or as a data input for demultiplexing applications. While the enable input is held high, all four outputs are high independently of the other inputs. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN CONNECTIONS (top view)



NC =
No Internal
Connection

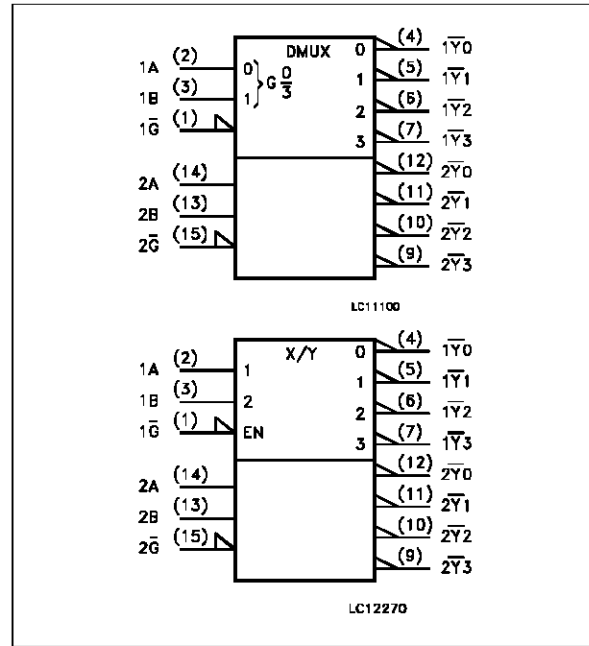
TRUTH TABLE

INPUTS			OUTPUTS				SELECTED OUTPUT
ENABLE	SELECT		\bar{Y}_0	\bar{Y}_1	\bar{Y}_2	\bar{Y}_3	
\bar{G}	B	A					
H	X	X	H	H	H	H	NONE
L	L	L	L	H	H	H	\bar{Y}_0
L	L	H	H	L	H	H	\bar{Y}_1
L	H	L	H	H	L	H	\bar{Y}_2
L	H	H	H	H	H	L	\bar{Y}_3

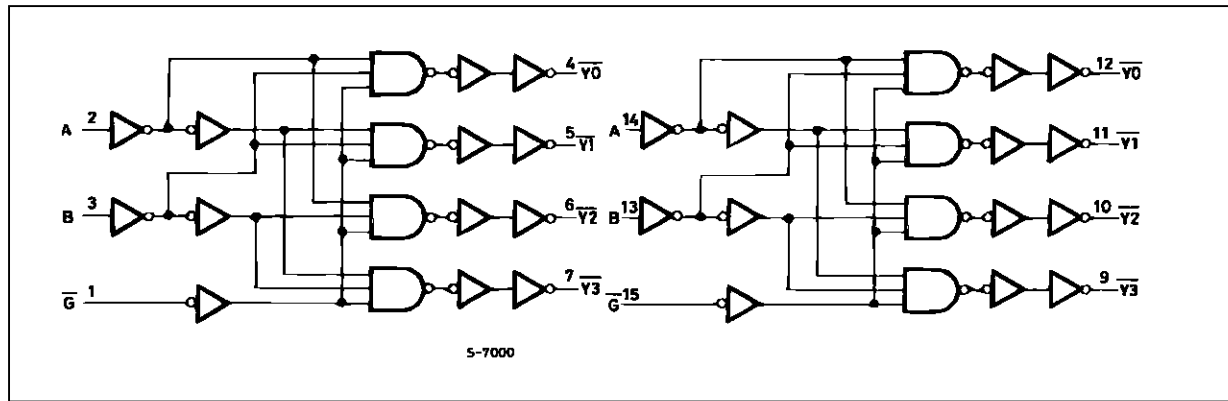
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 15	1G, 2G	Enable Inputs
2, 3	1A, 1B	Address Inputs
4, 5, 6, 7	1 \bar{Y}_0 to 1 \bar{Y}_3	Outputs
12, 11, 10, 9	2 \bar{Y}_0 to 2 \bar{Y}_3	Outputs
14, 13	2A, 2B	Address Inputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



SCHEMATIC CIRCUIT



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≅ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage	2 to 6	V	
V_I	Input Voltage	0 to V_{CC}	V	
V_O	Output Voltage	0 to V_{CC}	V	
T_{op}	Operating Temperature: M54HC Series M74HC Series	-55 to +125 -40 to +85	°C °C	
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 2\text{ V}$	0 to 1000	ns
		$V_{CC} = 4.5\text{ V}$	0 to 500	
		$V_{CC} = 6\text{ V}$	0 to 400	

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value						Unit		
				$T_A = 25\text{ °C}$ 54HC and 74HC			$-40\text{ to }85\text{ °C}$ 74HC		$-55\text{ to }125\text{ °C}$ 54HC			
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.	
V_{IH}	High Level Input Voltage	2.0 4.5 6.0		1.5			1.5		1.5		V	
				3.15			3.15		3.15			
				4.2			4.2		4.2			
V_{IL}	Low Level Input Voltage	2.0 4.5 6.0				0.5		0.5		0.5	V	
						1.35		1.35		1.35		
						1.8		1.8		1.8		
V_{OH}	High Level Output Voltage	2.0 4.5 6.0 4.5 6.0	$V_I = V_{IH}$ or V_{IL}	$I_O = -20\text{ }\mu\text{A}$	1.9	2.0		1.9		1.9		V
					4.4	4.5		4.4		4.4		
					5.9	6.0		5.9		5.9		
				$I_O = -4.0\text{ mA}$	4.18	4.31		4.13		4.10		
					$I_O = -5.2\text{ mA}$	5.68	5.8		5.63		5.60	
V_{OL}	Low Level Output Voltage	2.0 4.5 6.0 4.5 6.0	$V_I = V_{IH}$ or V_{IL}	$I_O = 20\text{ }\mu\text{A}$			0.0	0.1		0.1		0.1
						0.0	0.1		0.1		0.1	
						0.0	0.1		0.1		0.1	
				$I_O = 4.0\text{ mA}$		0.17	0.26		0.33		0.40	
					$I_O = 5.2\text{ mA}$		0.18	0.26		0.33		0.40
I_I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND				± 0.1		± 1		± 1	μA
I_{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			4		40		80	μA	

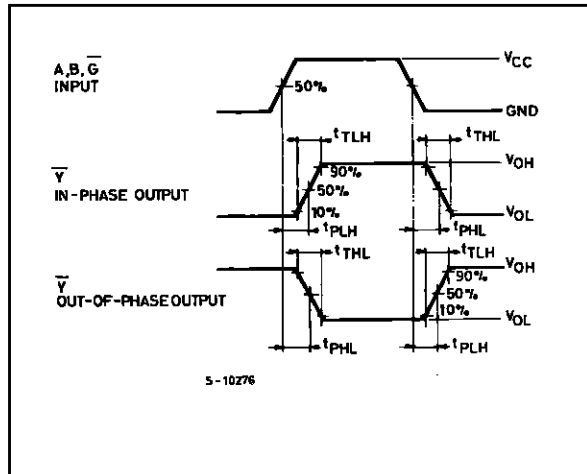
M54/M74HC139

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

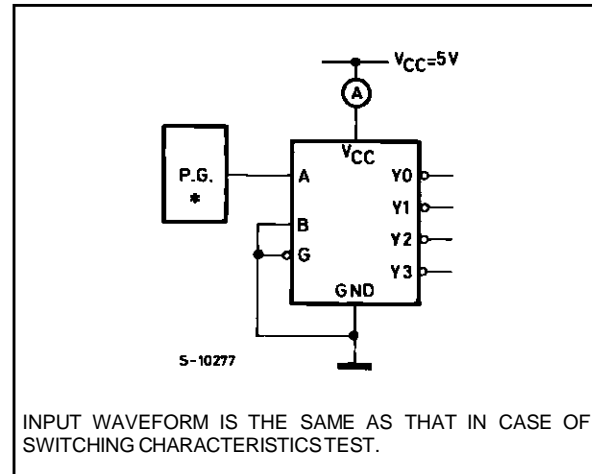
Symbol	Parameter	Test Conditions		Value						Unit	
		V_{CC} (V)		$T_A = 25 \text{ }^\circ\text{C}$ 54HC and 74HC			$-40 \text{ to } 85 \text{ }^\circ\text{C}$ 74HC		$-55 \text{ to } 125 \text{ }^\circ\text{C}$ 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t_{TLH} t_{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t_{PLH} t_{PHL}	Propagation Delay Time (A, B - Y)	2.0			45	130		165		195	ns
		4.5			15	26		33		39	
		6.0			13	22		28		33	
t_{PLH} t_{PHL}	Propagation Delay Time (G - Y)	2.0			39	110		140		165	ns
		4.5			13	22		28		33	
		6.0			11	19		24		28	
C_{IN}	Input Capacitance				5	10		10		10	pF
$C_{PD} (*)$	Power Dissipation Capacitance				46						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

SWITCHING CHARACTERISTICS TEST CIRCUIT

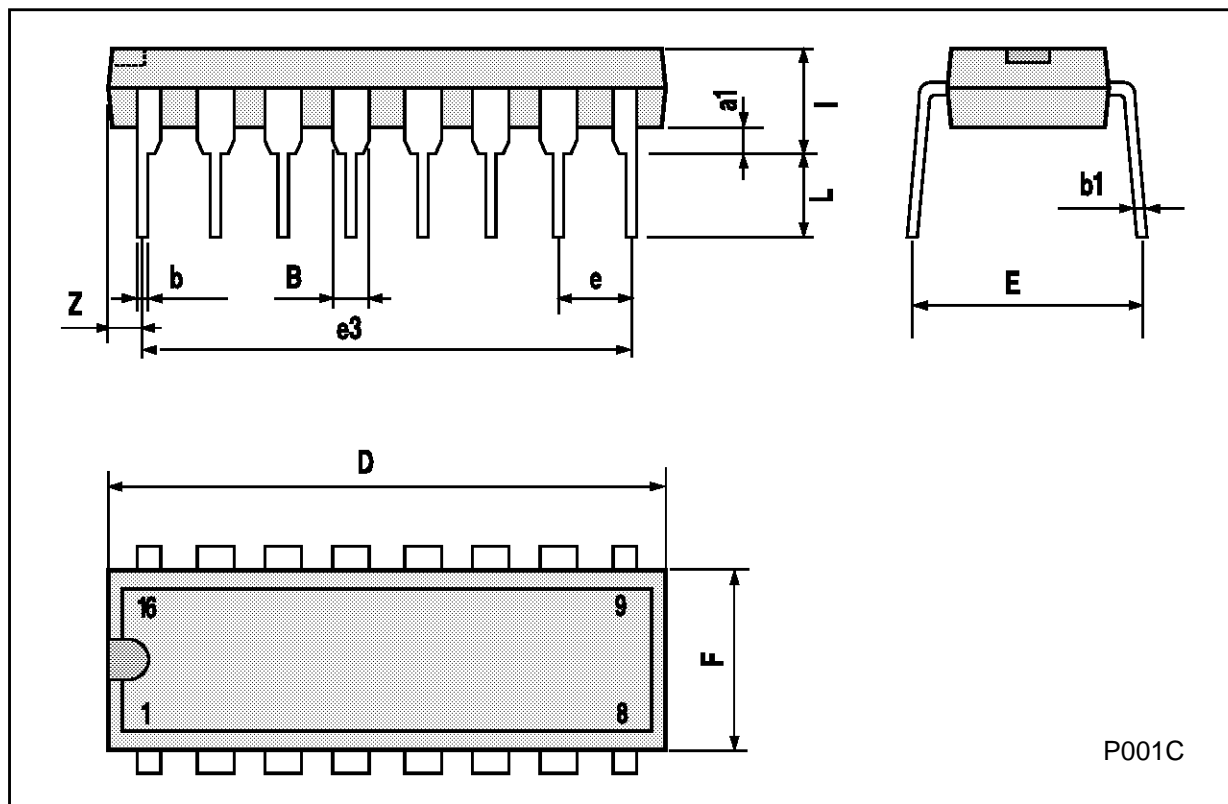


TEST CIRCUIT I_{CC} (Opr.)



Plastic DIP16 (0.25) MECHANICAL DATA

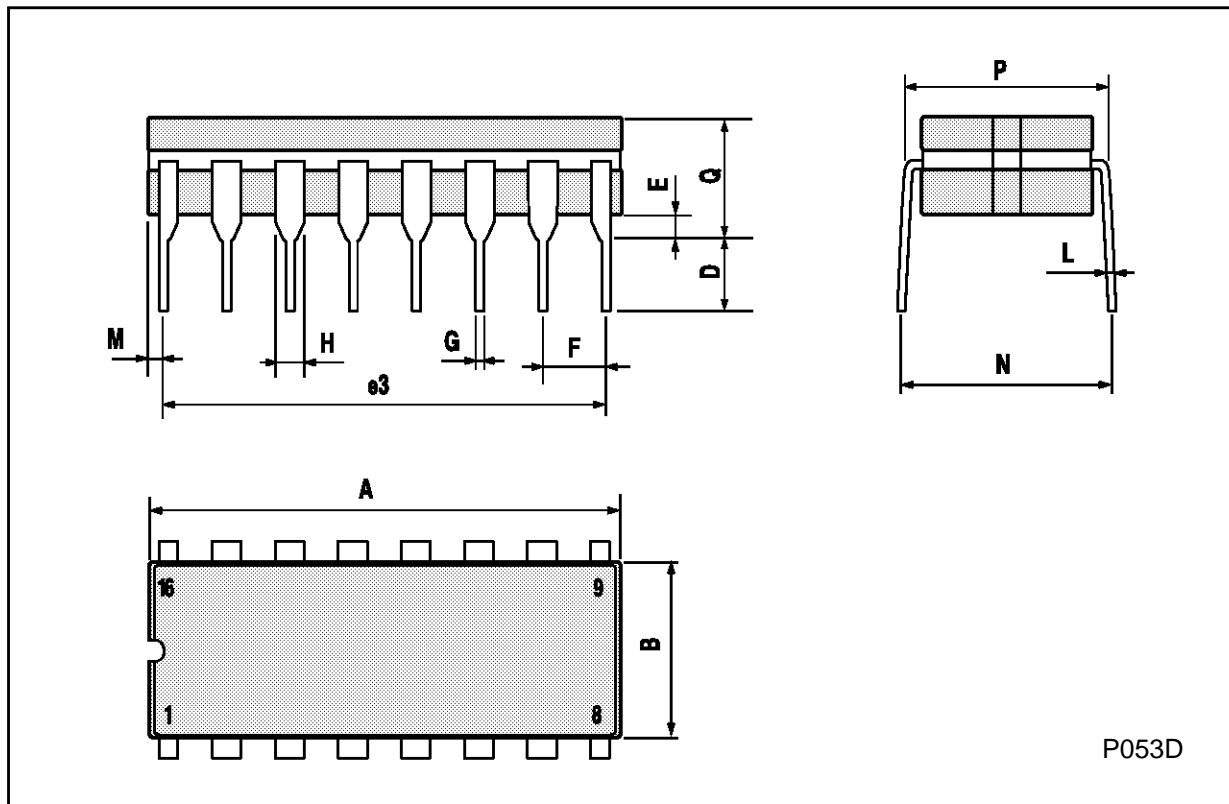
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C

Ceramic DIP16/1 MECHANICAL DATA

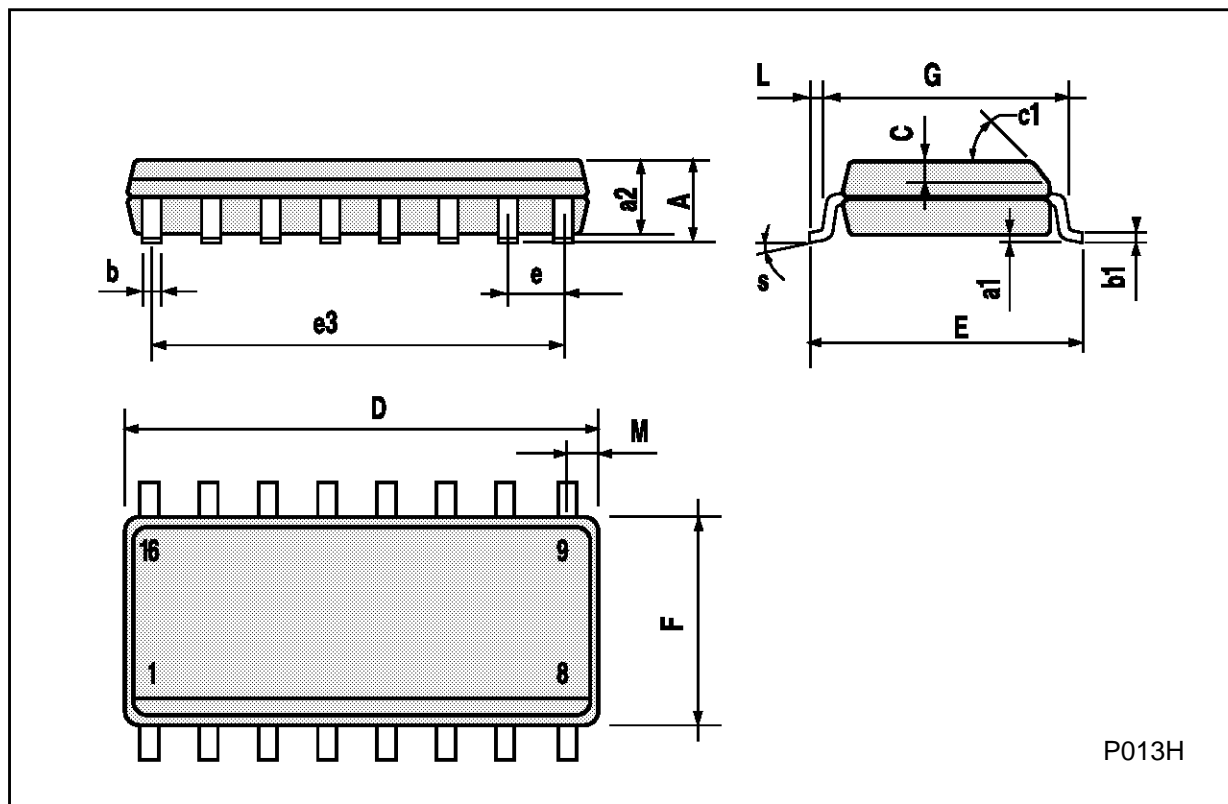
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053D

SO16 (Narrow) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



P013H

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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